

**TELECOMMUNICATION SYSTEM SECONDARY PROTECTION**

- **Ion-Implanted Breakdown Region**  
**Precise and Stable Voltage**  
**Low Voltage Overshoot under Surge**

| DEVICE | V <sub>(Z)</sub><br>V | V <sub>(BO)</sub><br>V |
|--------|-----------------------|------------------------|
| '1082L | - 58                  | - 82                   |

- **Planar Passivated Junctions**  
**Low Off-State Current < 10 µA**
- **Rated for International Surge Wave Shapes**

| WAVE SHAPE | STANDARD         | I <sub>TSP</sub><br>A |
|------------|------------------|-----------------------|
| 8/20 µs    | ANSI C62.41      | 150                   |
| 10/160 µs  | FCC Part 68      | 60                    |
| 10/560 µs  | FCC Part 68      | 45                    |
| 0.2/310 µs | RLM 88           | 38                    |
| 10/700 µs  | FTZ R12          | 50                    |
|            | VDE 0433         | 50                    |
|            | CCITT IX K17/K20 | 50                    |
| 10/1000 µs | REA PE-60        | 50                    |

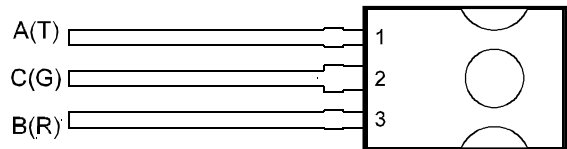
- **UL Recognized, E132482**

**description**

The TISP1082L is designed specifically for telephone line card protection against lightning and transients induced by a.c. power lines. These devices will suppress voltage transients between terminals A and C, B and C, and A and B.

Negative transients are initially clipped by zener action until the voltage rises to the breakover level, which causes the device to crowbar. The high crowbar holding current prevents d.c. latchup as the transient subsides. Positive transients are clipped by diode action.

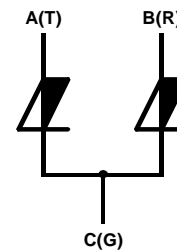
**L PACKAGE**  
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDXXAO

**device symbol**



These monolithic protection devices are fabricated in ion-implanted planar structures to ensure precise and matched breakover control and are virtually transparent to the system in normal operation.

**PRODUCT INFORMATION**

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.



# TISP1082L

## DUAL ASYMMETRICAL TRANSIENT VOLTAGE SUPPRESSORS

FEBRUARY 1990 - REVISED SEPTEMBER 1997

### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

| RATING   | SYMBOL     | VALUE       | UNIT       |
|--|------------|-------------|------------|
| Non-repetitive peak on-state pulse current (see Notes 1, 2 and 3)                        | $I_{TSP}$  | 150         | A          |
| 8/20 $\mu$ s (ANSI C62.41, open-circuit voltage wave shape 1.2/50 $\mu$ s)               |            | 60          |            |
| 10/160 $\mu$ s (FCC Part 68, open-circuit voltage wave shape 10/160 $\mu$ s)             |            | 50          |            |
| 5/200 $\mu$ s (VDE 0433, open-circuit voltage wave shape 2 kV, 10/700 $\mu$ s)           |            | 38          |            |
| 0.2/310 $\mu$ s (RLM 88, open-circuit voltage wave shape 1.5 kV, 0.5/700 $\mu$ s)        |            | 50          |            |
| 5/310 $\mu$ s (CCITT IX K17/K20, open-circuit voltage wave shape 2 kV, 10/700 $\mu$ s)   |            | 50          |            |
| 5/310 $\mu$ s (FTZ R12, open-circuit voltage wave shape 2 kV, 10/700 $\mu$ s)            |            | 45          |            |
| 10/560 $\mu$ s (FCC Part 68, open-circuit voltage wave shape 10/560 $\mu$ s)             |            | 50          |            |
| 10/1000 $\mu$ s (REA PE-60, open-circuit voltage wave shape 10/1000 $\mu$ s)             |            |             |            |
| Non-repetitive peak on-state current, 50 Hz, 0.7 s (see Notes 1 and 2)                   | $I_{TSM}$  | 10          | A rms      |
| Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A | $di_T/dt$  | 250         | A/ $\mu$ s |
| Junction temperature   | $T_J$      | 150         | °C         |
| Operating free - air temperature range   |            | 0 to 70     | °C         |
| Storage temperature range  | $T_{stg}$  | -40 to +150 | °C         |
| Lead temperature 1.5 mm from case for 10 s   | $T_{lead}$ | 260         | °C         |

- NOTES: 1. Above 70°C, derate linearly to zero at 150°C case temperature  
 2. This value applies when the initial case temperature is at (or below) 70°C. The surge may be repeated after the device has returned to thermal equilibrium.  
 3. Most PTT's quote an unloaded voltage waveform. In operation the TISP essentially shorts the generator output. The resulting loaded current waveform is specified.

### electrical characteristics for the A and B terminals, $T_J = 25^\circ\text{C}$

| PARAMETER                       | TEST CONDITIONS                  | MIN      | TYP | MAX      | UNIT          |
|---------------------------------|----------------------------------|----------|-----|----------|---------------|
| $V_Z$ Reference zener voltage   | $I_Z = \pm 1\text{mA}$           | $\pm 58$ |     |          | V             |
| $I_D$ Off-state leakage current | $V_D = \pm 50\text{V}$           |          |     | $\pm 10$ | $\mu\text{A}$ |
| $C_{off}$ Off-state capacitance | $V_D = 0$ f = 1 kHz (see Note 4) |          | 1   | 5        | pF            |

- NOTE 4: These capacitance measurements employ a three terminal capacitance bridge incorporating a guard circuit. The third terminal is connected to the guard terminal of the bridge.

### electrical characteristics for the A and C or the B and C terminals, $T_J = 25^\circ\text{C}$

| PARAMETER   | TEST CONDITIONS                        | MIN    | TYP   | MAX   | UNIT          |
|---|--|--------|-------|-------|---------------|
| $V_Z$ Reference zener voltage                             | $I_Z = -1\text{mA}$                    | - 58   |       |       | V             |
| $\alpha V_Z$ Temperature coefficient of reference voltage |  |        | 0.1   |       | %/°C          |
| $V_{(BO)}$ Breakover voltage                              | (see Notes 5 and 6)                    |        |       | - 82  | V             |
| $I_{(BO)}$ Breakover current                              | (see Note 5)                           | - 0.15 |       | - 0.6 | A             |
| $V_F$ Forward voltage                                     | $I_F = 5\text{A}$ (see Notes 5 and 6)  |        |       | 3     | V             |
| $V_{TM}$ Peak on-state voltage                            | $I_T = -5\text{A}$ (see Notes 5 and 6) |        | - 2.2 | - 3   | V             |
| $I_H$ Holding current                                     | (see Note 5)                           | - 150  |       |       | mA            |
| $dv/dt$ Critical rate of rise of off-state voltage        | (see Note 7)                           |        |       | - 5   | kV/ $\mu$ s   |
| $I_D$ Off-state leakage current                           | $V_D = -50\text{V}$                    |        |       | - 10  | $\mu\text{A}$ |
| $C_{off}$ Off-state capacitance                           | $V_D = 0$ f = 1 kHz (see Note 4)       |        | 300   | 500   | pF            |

- NOTES: 5. These parameters must be measured using pulse techniques,  $t_w = 100\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 6. These parameters are measured with voltage sensing contacts separate from the current carrying contacts located within 3.2 mm (0.125 inch) from the device body.  
 7: Linear rate of rise, maximum voltage limited to 80 %  $V_Z$  (minimum)..

## PRODUCT INFORMATION

PARAMETER MEASUREMENT INFORMATION

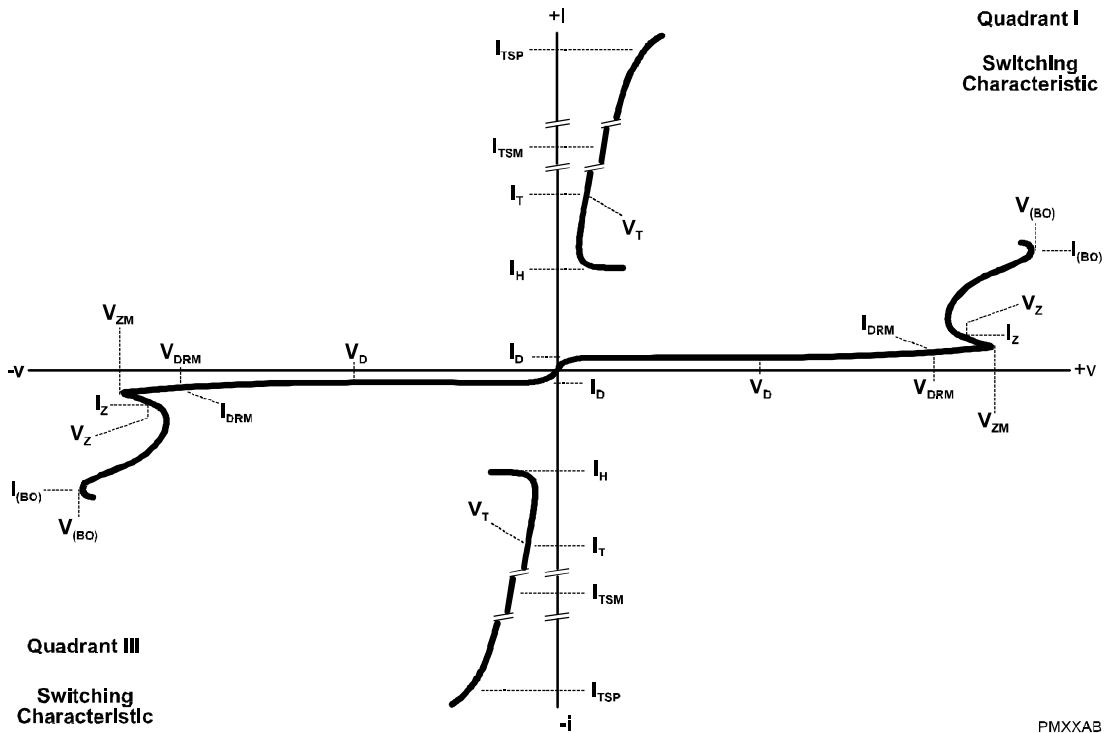


Figure 1. VOLTAGE-CURRENT CHARACTERISTIC FOR TERMINALS A AND B

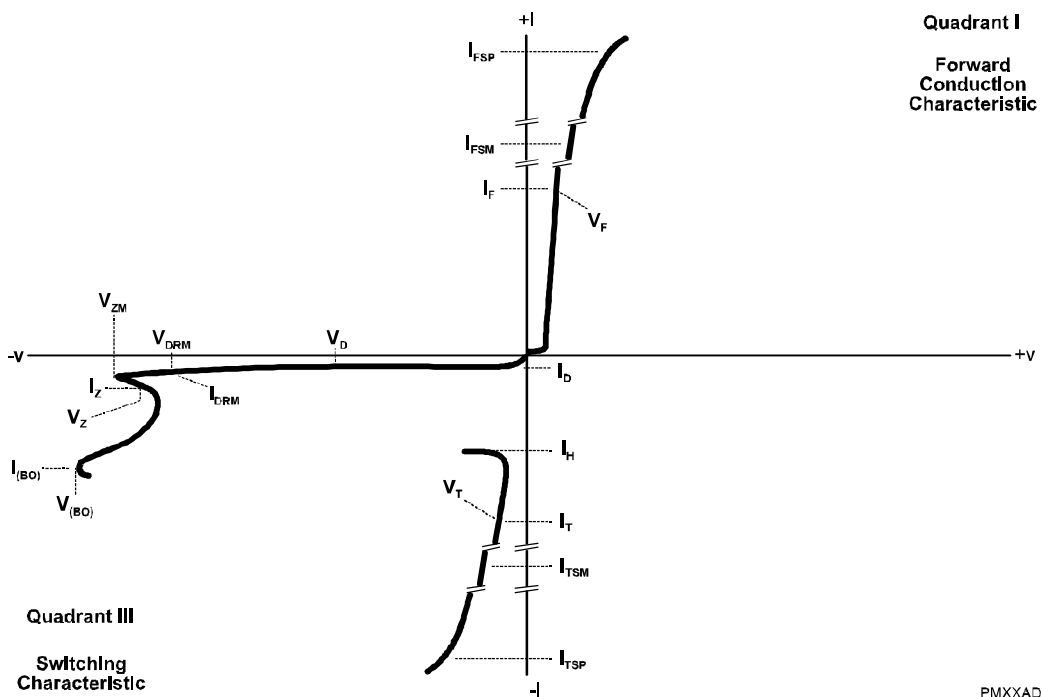


Figure 2. VOLTAGE-CURRENT CHARACTERISTIC FOR TERMINALS A AND C OR B AND C†

†Polarity is determined at terminal A or B with respect to C

# TISP1082L DUAL ASYMMETRICAL TRANSIENT VOLTAGE SUPPRESSORS

FEBRUARY 1990 - REVISED SEPTEMBER 1997

---

## thermal characteristics

| PARAMETER   | MIN | TYP | MAX | UNIT          |
|---|-----|-----|-----|---------------|
| $R_{\theta JA}$ Junction to free air thermal resistance |     |     | 100 | $^{\circ}C/W$ |



**TISP1082L**  
**DUAL ASYMMETRICAL TRANSIENT**  
**VOLTAGE SUPPRESSORS**

FEBRUARY 1990 - REVISED SEPTEMBER 1997

---

**IMPORTANT NOTICE**

Power Innovations Limited (PI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to verify, before placing orders, that the information being relied on is current.

PI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with PI's standard warranty. Testing and other quality control techniques are utilized to the extent PI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except as mandated by government requirements.

PI accepts no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor is any license, either express or implied, granted under any patent right, copyright, design right, or other intellectual property right of PI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

PI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS.

Copyright © 1997, Power Innovations Limited